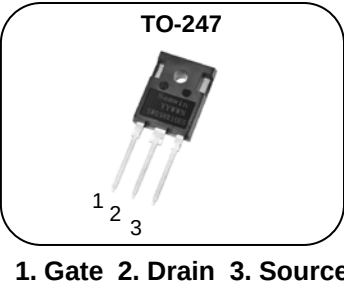


N-channel Enhanced mode TO-247 MOSFET

Features

- High ruggedness
- Low $R_{DS(ON)}$ (Typ 3.6mΩ)@ $V_{GS}=10V$
- Low Gate Charge (Typ 132nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application:Synchronous Rectification, Inverter , Li Battery Protect Board



BV_{DSS} : 100V
 I_D : 120A
 $R_{DS(ON)}$: 3.6mΩ

A schematic symbol for an N-channel MOSFET, showing the gate, drain, and source terminals.



General Description

This power MOSFET is produced with advanced technology of SAMWIN. This technology enable the power MOSFET to have better characteristics, including fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW T 038R10ES	SW038R10ES	TO-247	TUBE

Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DSS}	Drain to source voltage	100	V
I_D	Continuous drain current (@ $T_c=25^{\circ}C$)	120*	A
	Continuous drain current (@ $T_c=100^{\circ}C$)	110*	A
I_{DM}	Drain current pulsed (note 1)	480	A
V_{GS}	Gate to source voltage	± 20	V
E_{AS}	Single pulsed avalanche energy (note 2)	1126	mJ
E_{AR}	Repetitive avalanche energy (note 1)	106	mJ
dv/dt	Peak diode recovery dv/dt (note 3)	5	V/ns
P_D	Total power dissipation (@ $T_c=25^{\circ}C$)	250	W
	Derating factor above 25°C	2	W/°C
T_{STG}, T_J	Operating junction temperature & storage temperature	-55 ~ + 150	°C
T_L	Maximum lead temperature for soldering purpose, 1/8 from case for 5 seconds.	300	°C

*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value	Unit
R_{thjc}	Thermal resistance, Junction to case	0.50	°C/W
R_{thja}	Thermal resistance, Junction to ambient	35	°C/W

Electrical characteristic ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	100			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$, referenced to 25°C		0.05		V/ $^\circ\text{C}$
I_{DSS}	Drain to source leakage current	$V_{DS}=100V, V_{GS}=0V$			1	μA
		$V_{DS}=80V, T_J=125^\circ\text{C}$			50	μA
I_{GSS}	Gate to source leakage current, forward	$V_{GS}=20V, V_{DS}=0V$			100	nA
	Gate to source leakage current, reverse	$V_{GS}=-20V, V_{DS}=0V$			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=10V, I_D=60A, T_J=25^\circ\text{C}$		3.6	4.5	m Ω
		$V_{GS}=10V, I_D=120A, T_J=25^\circ\text{C}$		3.7	4.6	m Ω
		$V_{GS}=10V, I_D=60A, T_J=125^\circ\text{C}$		5.8		m Ω
G_{fs}	Forward transconductance	$V_{DS}=8V, I_D=60A$		121		S
Dynamic characteristics						
C_{iss}	Input capacitance	$V_{GS}=0V, V_{DS}=50V, f=1\text{MHz}$		8450		pF
C_{oss}	Output capacitance			1050		
C_{rss}	Reverse transfer capacitance			15		
$t_{d(on)}$	Turn on delay time	$V_{DS}=50V, I_D=30A, R_G=4.7\Omega, V_{GS}=10V$ (note 4,5)		49		ns
t_r	Rising time			62		
$t_{d(off)}$	Turn off delay time			92		
t_f	Fall time			44		
Q_g	Total gate charge	$V_{DS}=80V, V_{GS}=10V, I_D=30A$ (note 4,5)		132		nC
Q_{gs}	Gate-source charge			35		
Q_{gd}	Gate-drain charge			43		
R_g	Gate resistance	$V_{DS}=0V$, Scan F mode		1.9		Ω

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			120	A
I_{SM}	Pulsed source current				480	A
V_{SD}	Diode forward voltage drop.	$I_S=100A, V_{GS}=0V$			1.4	V
t_{rr}	Reverse recovery time	$I_S=30A, V_{GS}=0V, di/dt=100A/\mu s$		74		ns
Q_{rr}	Reverse recovery charge			149		nC

※. Notes

1. Repeattive rating : pulse width limited by junction temperature.
2. $L=2.5\text{mH}, I_{AS}=30A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
3. $I_{SD} \leq 30A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. Essentially independent of operating temperature.

Fig. 1. On-state characteristics

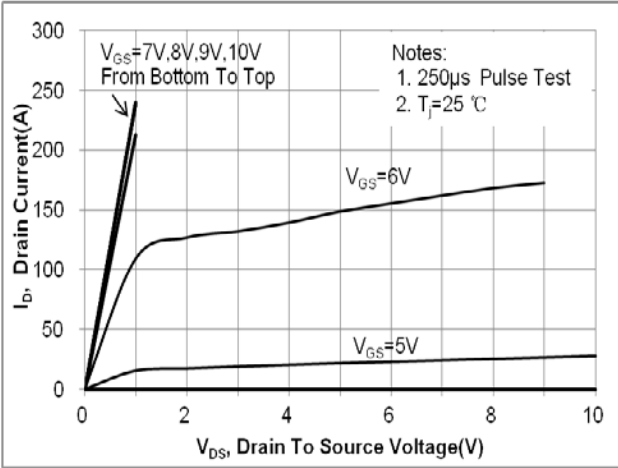


Fig. 2. Transfer Characteristics

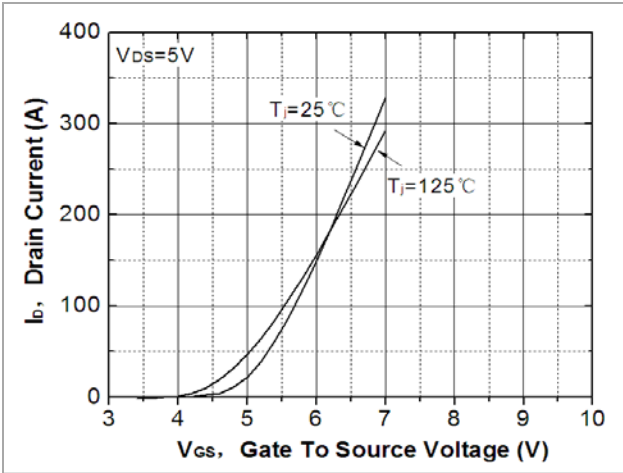


Fig. 3. On-resistance variation vs. drain current and gate voltage

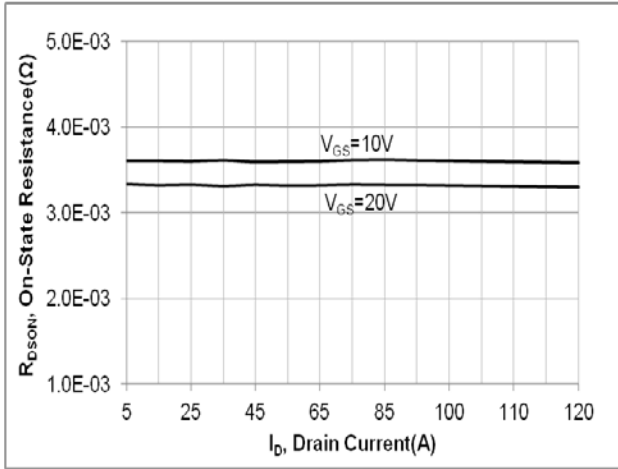


Fig. 4. On-state current vs. diode forward voltage

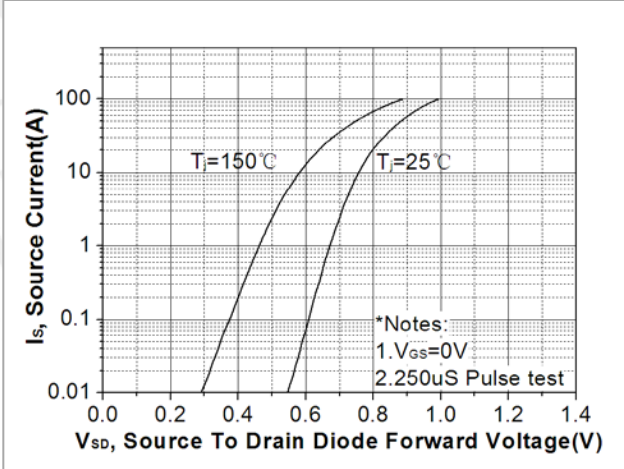


Fig 5. Breakdown voltage variation vs. junction temperature

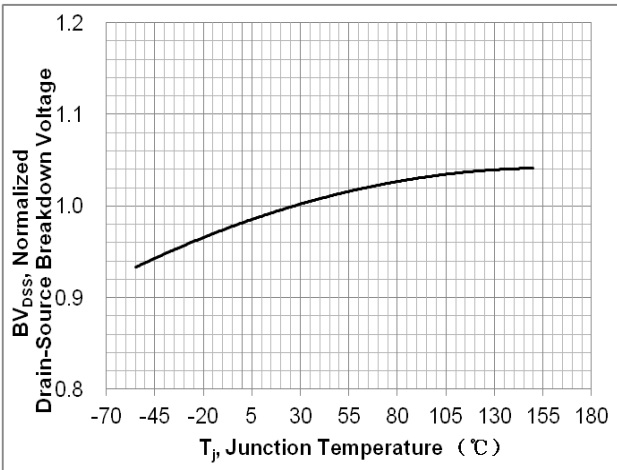


Fig. 6. On-resistance variation vs. junction temperature

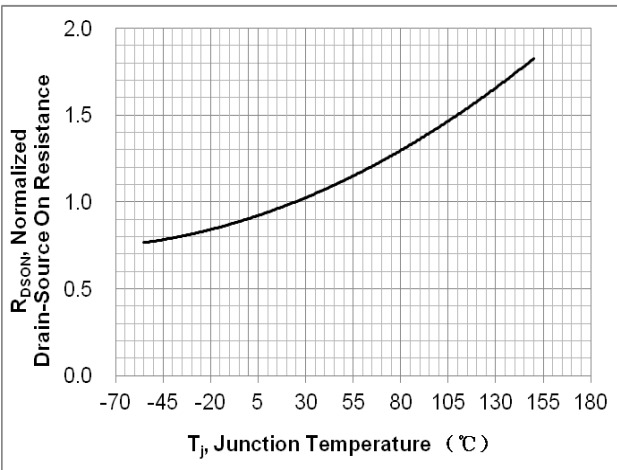


Fig. 7. Gate charge characteristics

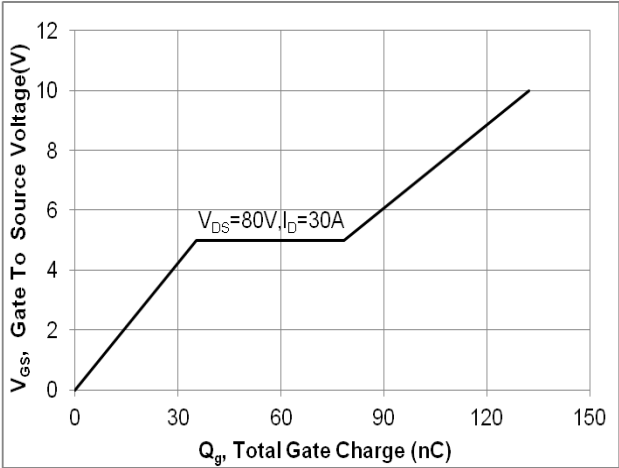


Fig. 8. Capacitance Characteristics

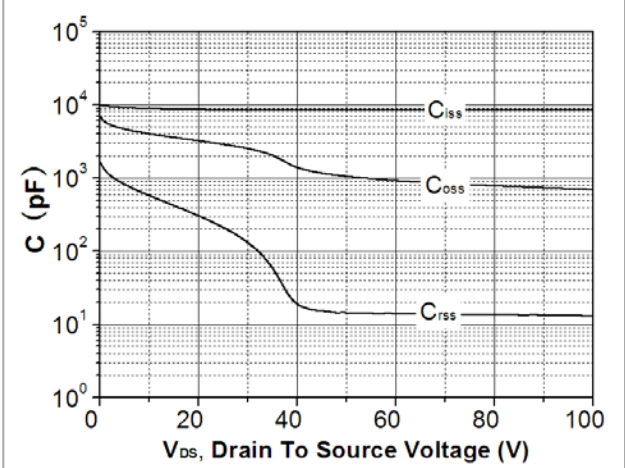


Fig. 9. Maximum safe operating area

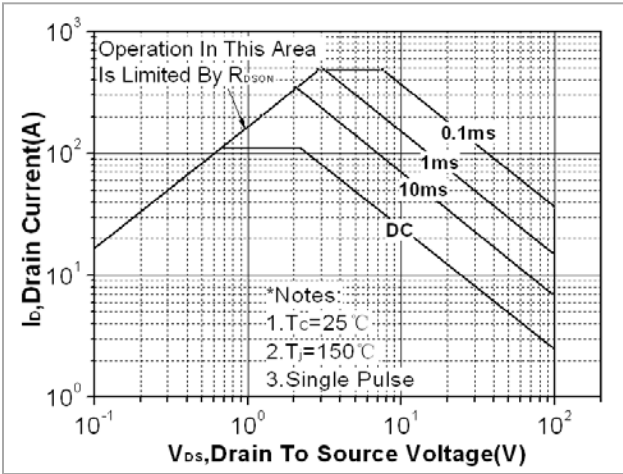


Fig. 10. Transient thermal response curve

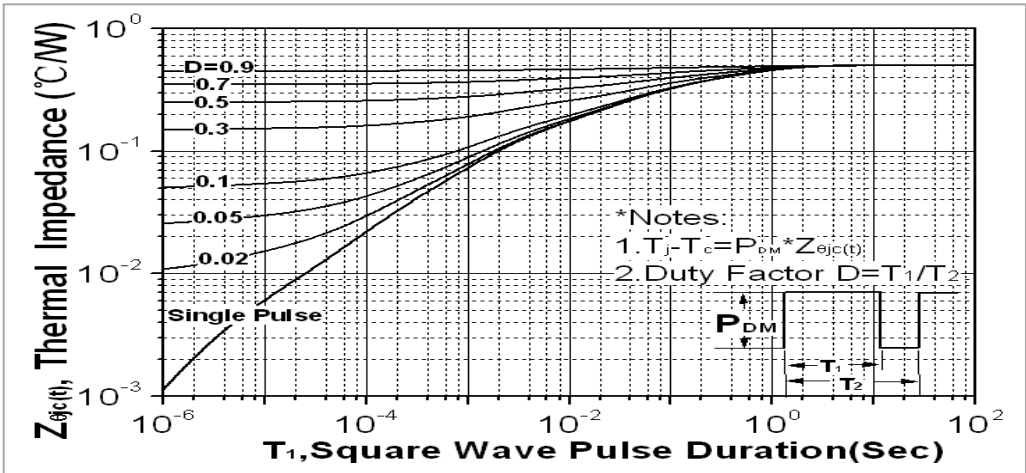


Fig. 11. Gate charge test circuit & waveform

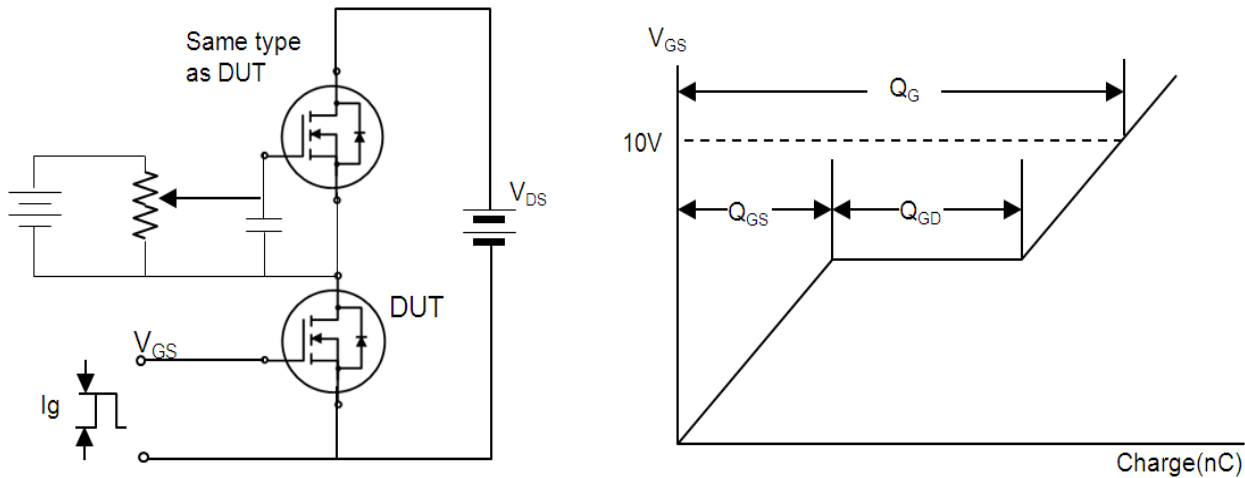


Fig. 12. Switching time test circuit & waveform

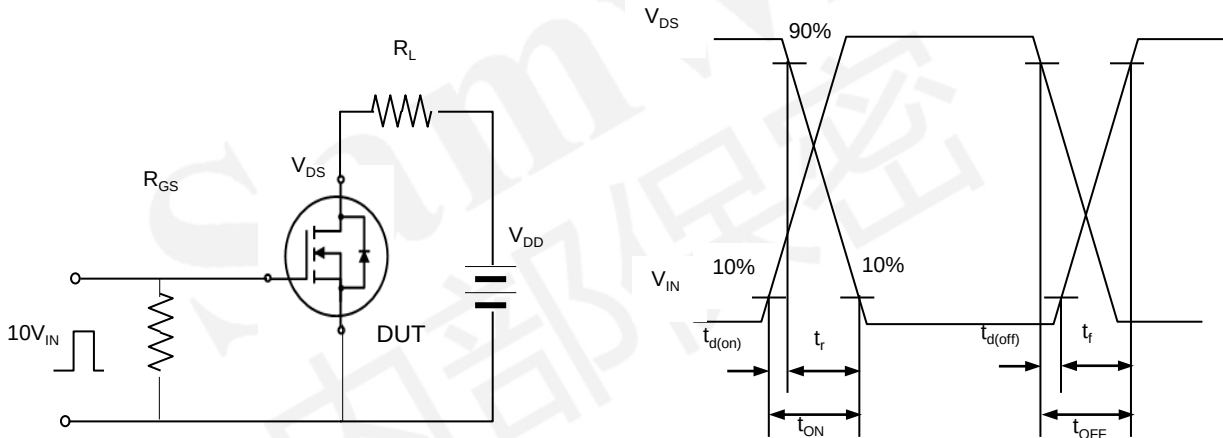


Fig. 13. Unclamped Inductive switching test circuit & waveform

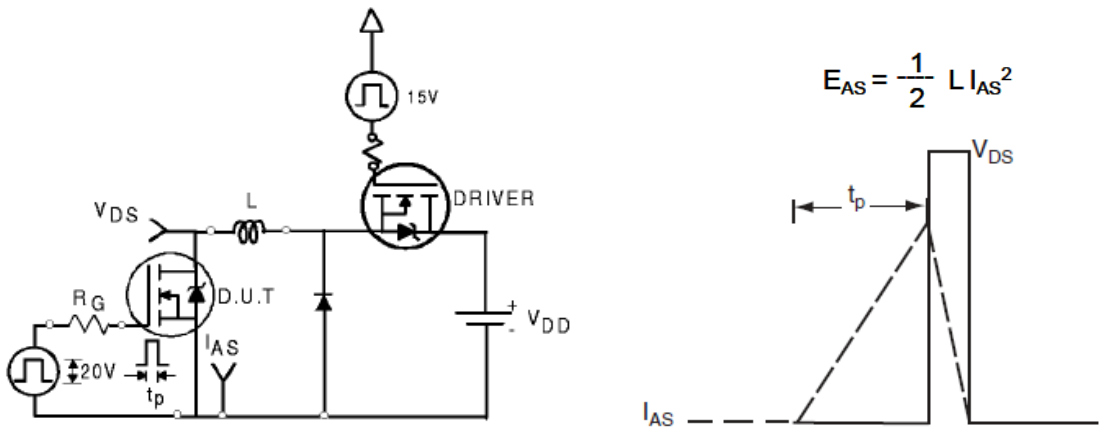
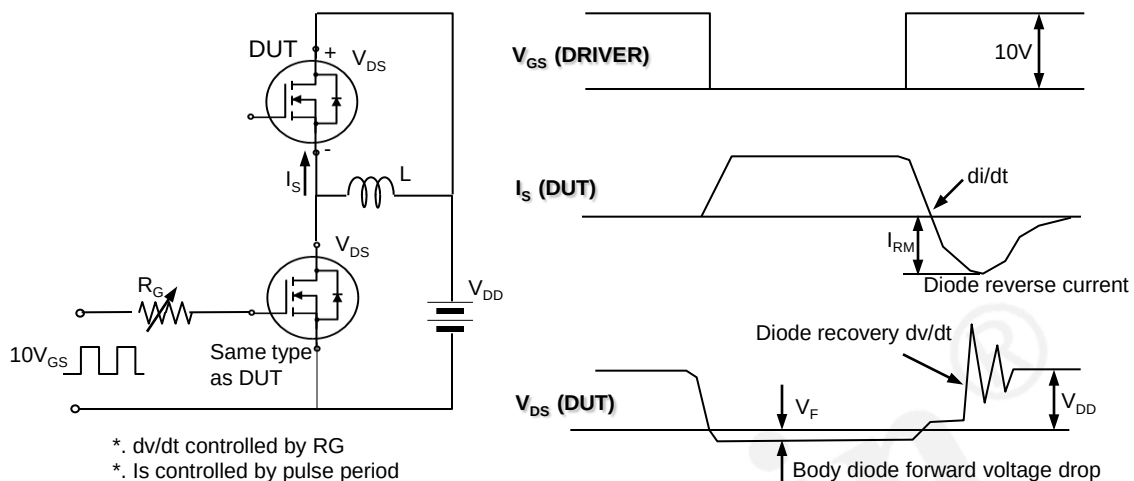


Fig. 14. Peak diode recovery dv/dt test circuit & waveform



DISCLAIMER

- * All the data & curve in this document was tested in XI'AN SEMIPOWER TESTING & APPLICATION CENTER.
- * This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
- * Qualification standards can also be found on the Web site (<http://www.semipower.com.cn>) 
- * Suggestions for improvement are appreciated, Please send your suggestions to samwin@samwinsemi.com